

Rev.A Nov.-2021

VRW5609 双N沟槽MOSFET

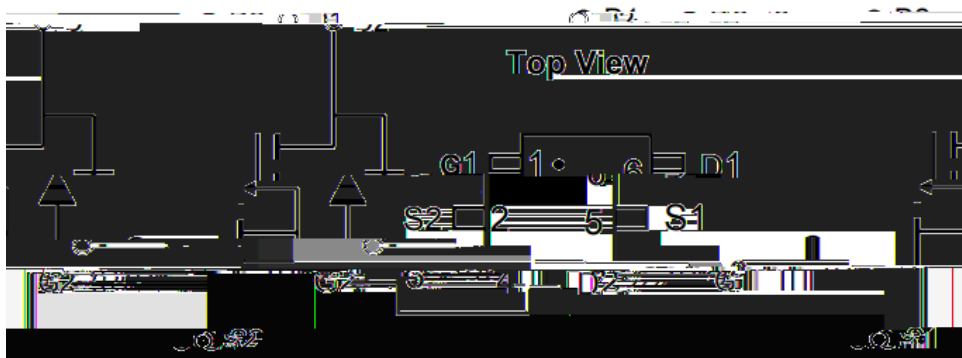
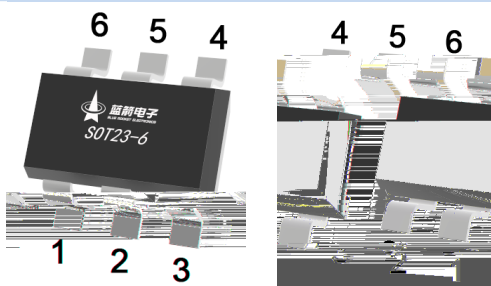
Dual N-Channel MOSFET in a SOT23-6 Plastic Package.

采用超密单元设计,低 $R_{DS(ON)}$,高可靠,高频产品。

Super high dense cell design for low $R_{DS(ON)}$, Rugged and reliable, HF product.

广泛应用于笔记本电脑,便携式设备及电池供电系统。

Power Management in Notebook computer, Portable Equipment and Battery powered systems.



PIN1 χ G1 PIN 2 χ S2 PIN 3 χ G2

PIN 4 χ D2 PIN 5 χ S1 PIN 6 χ D1

Marking

B4DH

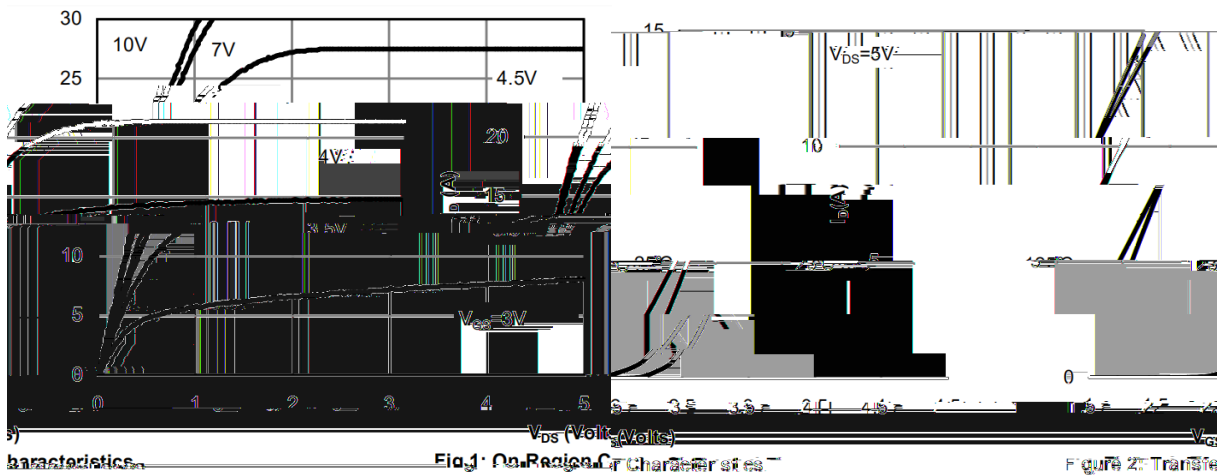
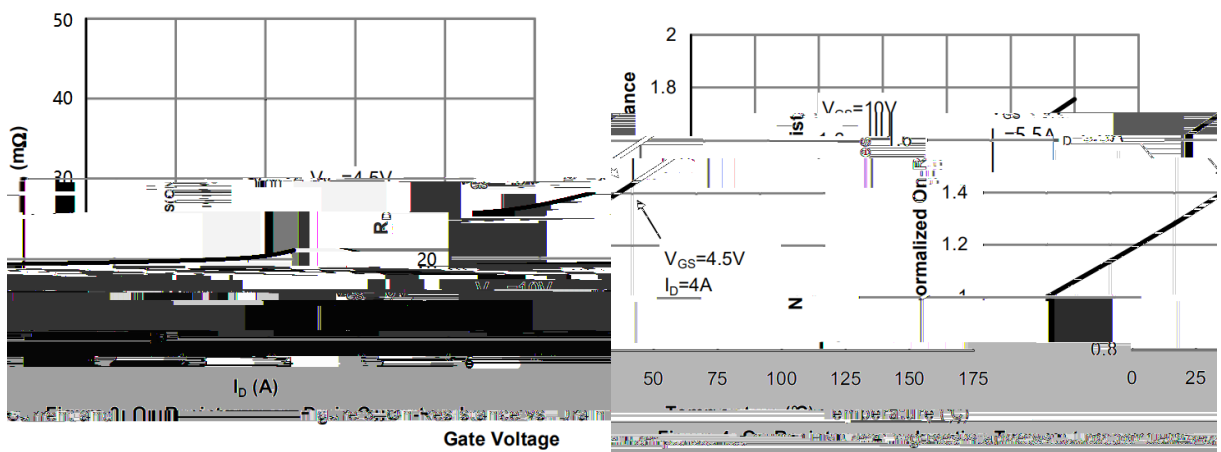
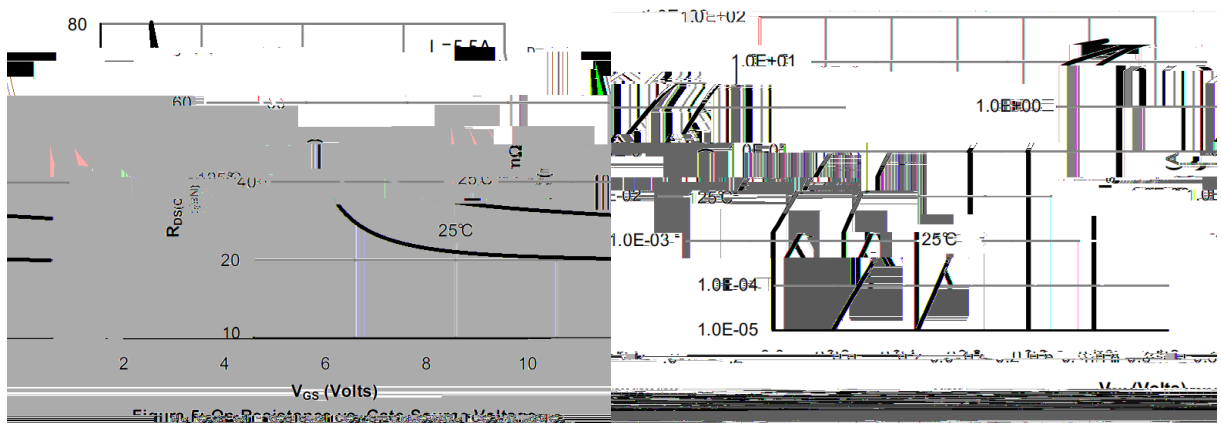
Rev.A Nov.-2021

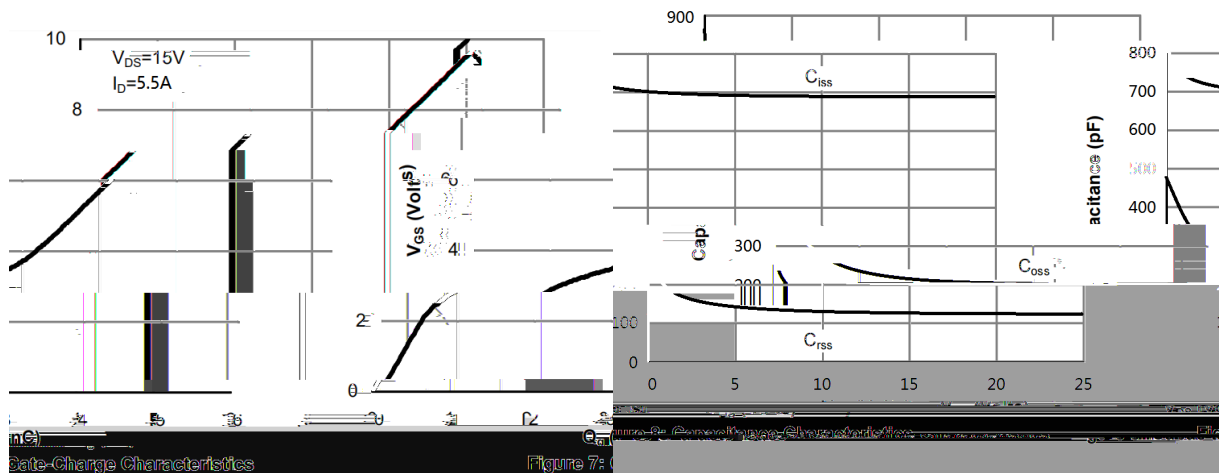
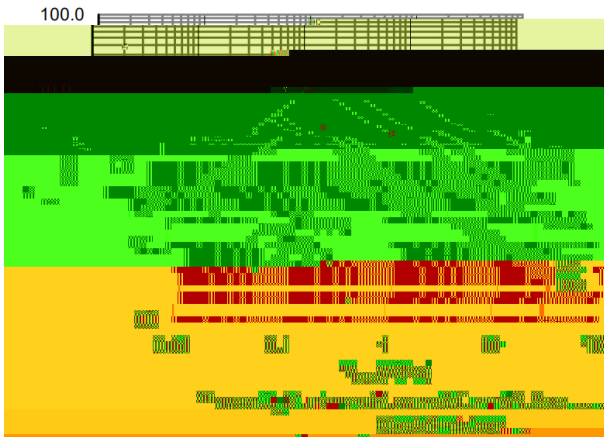
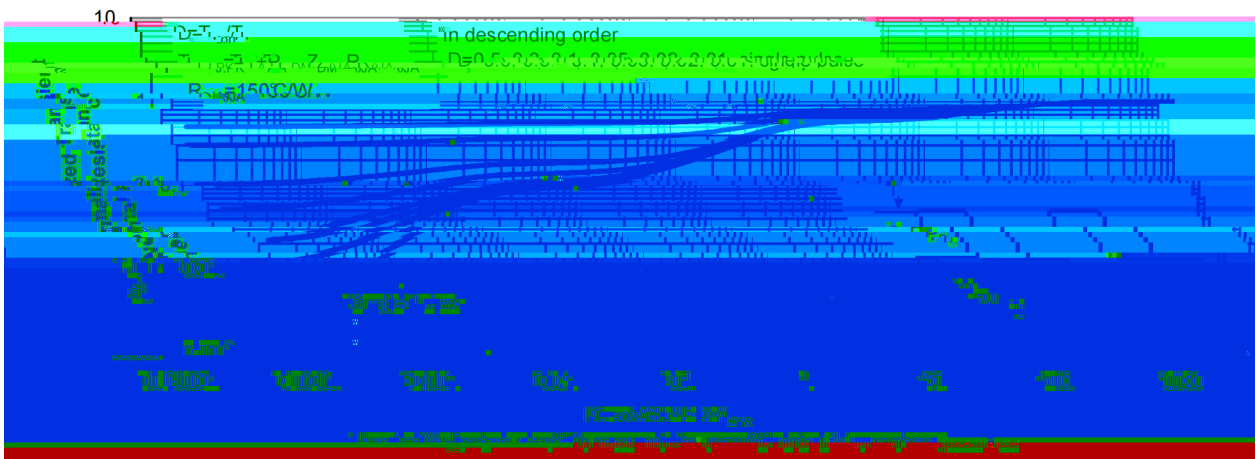
v _{DS} Parameter		I _D Symbol	P _D Rating	Unit
Drain-Source Voltage		V _{DSS}	30	V
Gate-Source Voltage		V _{GSS}	±20	V
Drain Current – Continuous		I _D	5.5	A
Pulsed Drain Current		I _{DM}	27.5	A
Power Dissipation		P _D	1.3	W
Storage Temperature Range		T _{stg}	-55 150	
Maximum Junction-to-Ambient	t ≤ 10s	R _{θJA}	95	/W
Maximum Junction-to-Ambient	Steady-State		150	
Maximum Junction-to-Lead	Steady-State	R _{θJL}	68	

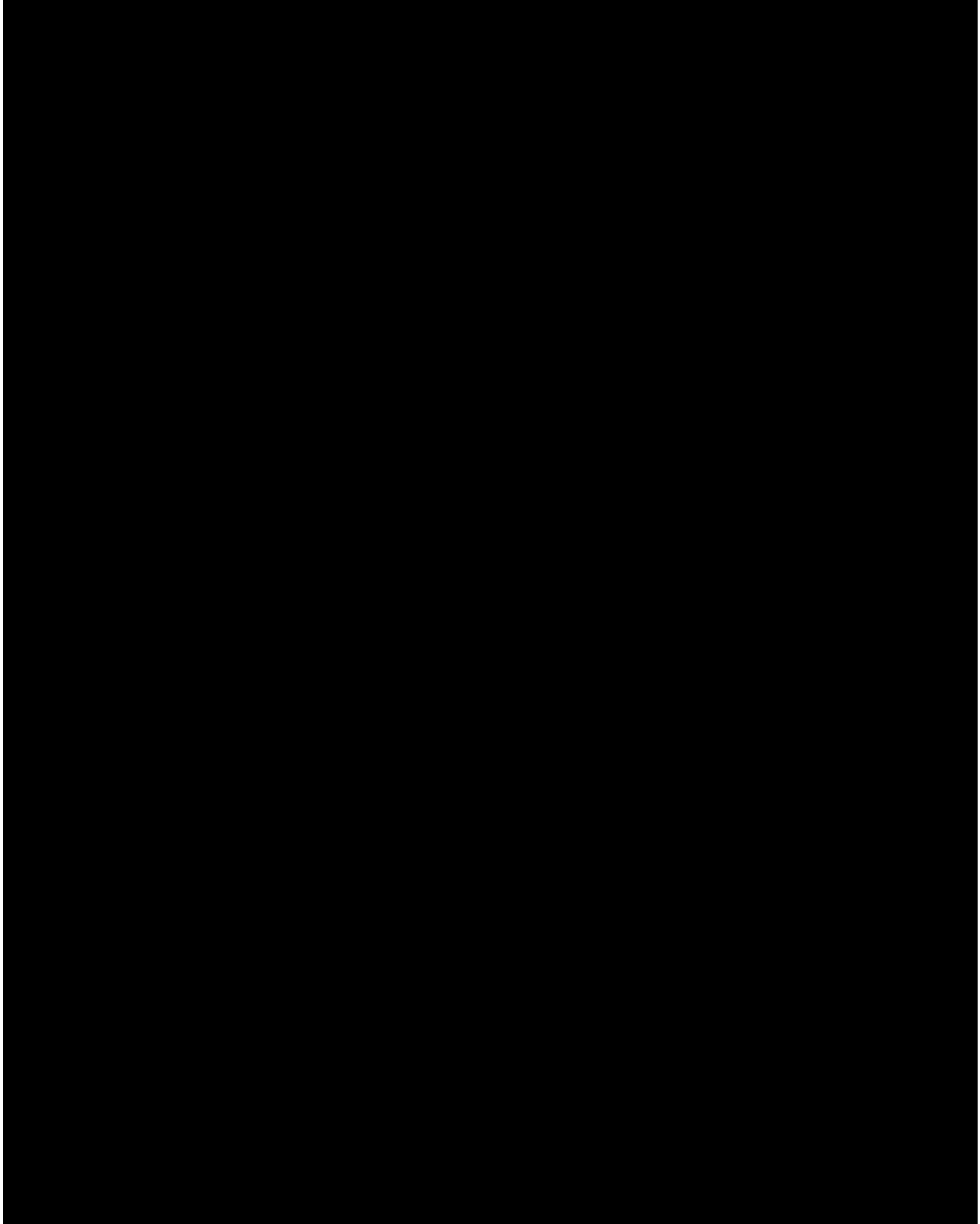
v _{DS} Parameter	I _D Symbol	Test Conditions	Min	Typ	Max	Unit
------------------------------	--------------------------	-----------------	-----	-----	-----	------

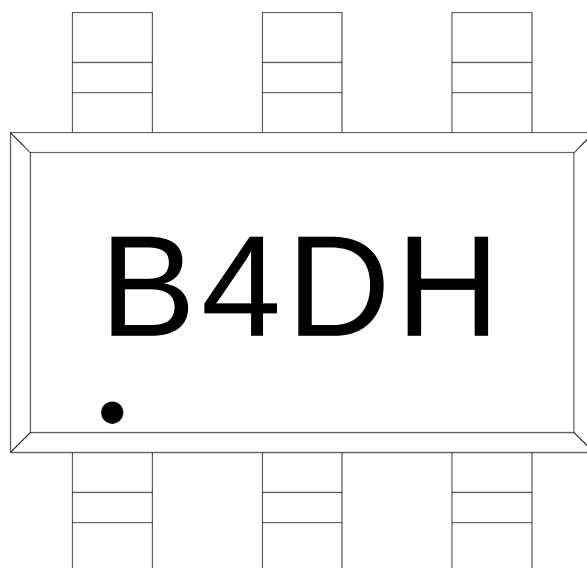
Rev.A Nov.-2021

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Capacitance	Ciss	V _{GS} =0V, f=1MHz V _{DS} =25V		690		pF
Output Capacitance	Coss			200		
Reverse Transfer Capacitance	Crss			130		
Gate resistance	Rg	V _{GS} =0V, f=1MHz V _{DS} =0V		3.0		Ω
Total Gate Charge	Q _{g(10V)}	V _{GS} =10V, I _D =5.5A V _{DS} =15V,		5.2		nC
Total Gate Charge	Q _{g(4.5V)}			2.5		
Gate Source Charge	Q _{gs}			0.8		
Gate Drain Charge	Q _{gd}			1.3		
Turn-On Delay Time	t _{d(on)}	V _{GS} =10V V _{DS} =15V R _L =3Ω R _{GEN} =3Ω		4.5		ns
Turn-On Rise Time	t _r			2.5		
Turn-Of						









符号

B4D: 产品代码

H: 公司代码

Note:

B4D 产品代码

H: 公司代码。

Rev.A Nov.-2021